

OK TO ENTER: /JSR/

**METHOD OF FORMING STORAGE NODES IN A DRAM**

Appl. No. : 09/851,580 Confirmation No. 3189  
Applicant : Jiunn-Ren Hwang et al.  
Filed : May 10, 2001  
TC/A.U. : 1795  
Examiner : Ruggles, John S  
Docket No. : NAUP0292USA  
Customer No. : 27765

Commissioner for Patents  
P.O. Box 1450  
Alexandria VA 22313-1450

**AMENDMENT**

5 Sir:

In response to the Office action of October 21, 2008, please amend the above-identified application as follows:

**Listing of the Claims** begins on page 2 of this paper.

**Amendments to the Drawings** begin on page 3 of this paper.

10 **Remarks/Arguments** begin on page 4 of this paper.

An **Appendix** including amended drawing figures is attached following page 5 of this paper.